

DUAL MONOLITHIC SPST CMOS/D-MOS T-CONFIGURATION ANALOG SWITCH

ORDERING INFORMATION

Dual SPST 'T' Switch, Logic '0' OFF, Break-before-make	14-Pin Plastic DIP	14-Pin Ceramic DIP
Commercial Temp. Range	CDG5341CJ	—
Industrial Temp. Range	CDG5341BJ	CDG5341BK
Military Temp. Range	—	CDG5341AK

FEATURES

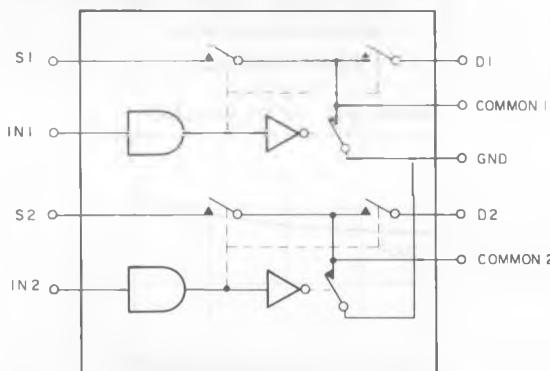
- Ultra High OFF Isolation, > 80 dB @ 10MHz
- Low Channel-to-Channel Crosstalk, > 80 dB @ 10MHz
- CMOS Compatible Inputs
- Low ON Resistance, <110Ω
- Wide Bandwidth, -1.0dB @ 50MHz

DESCRIPTION

Topaz Semiconductor CMOS/D-MOS Analog Switches feature high-speed, low-power 5V CMOS input logic and level translation circuitry and high speed, low capacitance Lateral D-MOS switches. CMOS and Lateral D-MOS circuitry are fabricated together on a single silicon chip.

All devices contain diodes to protect inputs against damage due to high static voltages or electric fields; however, it is advised that precautions be taken not to exceed the maximum recommended input voltages. All unused inputs must be connected to an appropriate logic level (either V_{cc} or GND).

FUNCTIONAL BLOCK DIAGRAM



Two SPST 'T' Switches per Package.

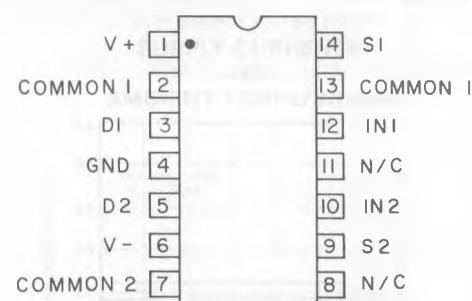
Switches shown in Logic '0' Input Position.

Compensation Networks can be connected to Common 1 and Common 2.

APPLICATIONS

- RF & Video Switches
- Data Acquisition

PIN CONFIGURATION



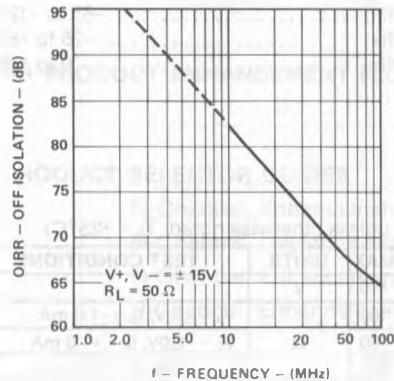
Top View

CDG5341AK
CDG5341BK
(See Package 14)

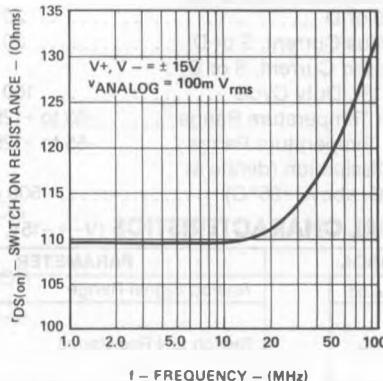
CDG5341BJ
CDG5341CJ
(See Package 9)

TYPICAL PERFORMANCE CHARACTERISTICS ($T_A = +25^\circ\text{C}$ unless otherwise specified)

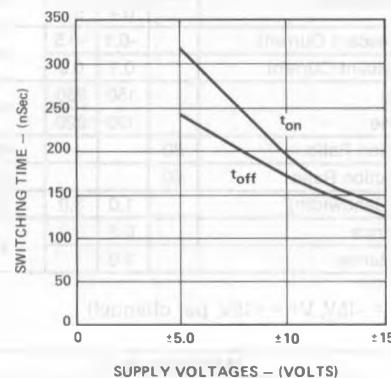
**OFF ISOLATION REJECTION RATIO
—VS—
FREQUENCY**



**SWITCH ON RESISTANCE
—VS—
FREQUENCY**



**SWITCHING TIMES
—VS—
SUPPLY VOLTAGES**



ABSOLUTE MAXIMUM RATINGS

V-	Negative Supply Voltage	-20V
V+	Positive Supply Voltage	+20V
V _{IN}	Control Input Voltage Range	V+ +0.3V, V- -0.3V
I _L	Continuous Current, any Pin Except S or D	20 mA
I _S	Continuous Current, S or D	30 mA
I _S	Peak Pulsed Current, S or D, 80μsec, 1%, Duty Cycle	100 mA
T _J	Junction Temperature Range	-55 to +125°C
T _S	Storage Temperature Range	-55 to +125°C
P _D	Power Dissipation (derate at 12mW/°C, above +85°C)	500 mW

RECOMMENDED OPERATING CONDITIONS

V-	Negative Supply Voltage	-8.0 to -15V
V+	Positive Supply Voltage	+8.0 to +15V
V _{IN}	Control Input Voltage Range	0 to +5V
V _S	Analog Switch Voltage Range	-10 to +10V
T _{OP}	Operating Temperature	(A Suffix)	-55 to +125°C
		(B Suffix)	-25 to +85°C
		(C Suffix)	0 to +70°C

ELECTRICAL CHARACTERISTICS (V₋ = -15V, V₊ = +15V per channel, unless otherwise noted, T_A = +25°C)

#	SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
1	V _{ANALOG}	S T A T I C	Analog Signal Range	-10	+10	V	
2	r _{DSON}		Switch ON Resistance	100	160	Ω	V _S = -10V, I _S = -1.0 mA
3				110	160		V _S = +2.0V, I _S = +1.0 mA
4				200	320		V _S = +10V, I _S = -1.0 mA
5	V _{IH}		High Level Input Voltage	4.5	3.4	V	
6	V _{IL}		Low Level Input Voltage		1.0		
7	I _{IN}		Logic Input Leakage Current	0.01	0.1	μA	V _{IN} = +5.0V
8				0.02	0.1		V _{IN} = +15V
9	I _{DIOFF}		Switch OFF Leakage Current	0.2	5.0	nA	V _D = +10V, V _S = -10V
10	I _{SIOFF}			0.4	5.0		V _S = +10V, V _D = -10V
11	I ₋		Negative Supply Quiescent Current	-0.1	-0.5	μA	V _{IN} = 0 or V ₊
12	I ₊		Positive Supply Quiescent Current	0.1	0.5		
13	t _{ON}	D Y N A M 	Switch Turn-On Time	150	250	nsec	V _{IN} = 5.0V
14	t _{OFF}		Switch Turn-OFF Time	120	220		
15	O _{IRR}		OFF Isolation, Rejection Ratio	80		dB	f = 10 MHz, R _L = 50Ω
16	C _{CRR}		Cross-Coupling Rejection Ratio	80		dB	f = 10 MHz, R _L = 50Ω
17			Frequency Roll-Off (Bandwidth)	1.0	3.0	dB	f = 50 MHz, R _L = 50Ω
18	C _d		Drain-Node Capacitance	0.3		pF	V _D = 0 f = 1MHz, V _{IN} = 0
19	C _s		Source-Node Capacitance		3.0		V _S = 0

ELECTRICAL CHARACTERISTICS (V₋ = -15V, V₊ = +15V, per channel)

LIMITS AT TEMPERATURE EXTREMES

#	SYMBOL	PARAMETER	MAXIMUM @ T _A =					UNITS	TEST CONDITIONS	
			-55°C	-25°C	70°C	+85°C	+125°C			
1	V _{ANALOG}	S T A T I C	Analog Signal Range	±10	±10	±10	±10	±10	V	
2	r _{DSON}			160	160	240	240	300		V _S = -10V, I _S = -1.0 mA
3			Switch On Resistance	160	160	240	240	300	Ω	V _S = +2.0V, I _S = +1.0 mA
4				320	320	480	480	600		V _S = +10V, I _S = -1.0 mA
5	I _{IN}		Logic Input Leakage Current	0.1	0.1	1.0	1.0	10	μA	V _{IN} = +5.0V
6				0.1	0.1	2.0	2.0	20		V _{IN} = +15V
7	I _{DIOFF}		Switch OFF Leakage Current	5.0	5.0	100	100	1000	nA	V _D = +10V, V _S = -10V
8	I _{SIOFF}			5.0	5.0	100	100	1000		V _S = +10V, V _D = -10V
9	I ₋		Supply Quiescent Currents	-0.5	-0.5	-20	-20	-100	μA	V _{IN} = 0 or V ₊
10	I ₊			0.5	0.5	20	20	100		